

D. Thin Film Process Technology 분과

2017년 2월 15일 (수), 12:40-14:25
Room A (에메랄드, 2층)

[WA3-D] ALD/CVD Thin Films

좌장: 민요셉(건국대학교), 박태주(한양대학교)

WA3-D-1 12:40-12:55	High Performance p-type Thin Film Transistors with Atomic Layer Deposited SnO Films In Hwan Baek ^{1,2} , Soo Hyun Kim ¹ , Jung Jun Pyeon ¹ , Taek Mo Chung ³ , Jeong Hwan Han ³ , Cheol Seong Hwang ² , and Seong Keun Kim ¹ <i>¹Center for Electronic Materials, Korea Institute of Science and Technology, ²Department of Materials Science and Engineering, and Inter-University Semiconductor Research Center, Seoul National University, ³Division of Advanced Materials, Korea Research</i>
WA3-D-2 12:55-13:10	Stabilization of Tetragonal Phase in Hf_{0.5}Zr_{0.5}O₂ Thin Films induced by Low Deposition Temperature during Atomic Layer Deposition Keum Do Kim, Min Hyuk Park, Yu Jin Kim, Han Joon Kim, Taehwan Moon, Seung Dam Hyun, Hyeonwoo Park, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University</i>
WA3-D-3 13:10-13:25	In Situ Suppression of Impurity Contamination for High Quality Thin Film Deposition Using Atmospheric Pressure PECVD Gwihyun Kim and Seung Jae Baik <i>Department of Electrical, Electronic, and Control Engineering, Hankyong National University</i>
WA3-D-4 13:25-13:40	Mechanism Study on The Atomic Layer Deposition of GeTe Films Using Ge[N[Si(CH₃)₃]₂]₂, {(CH₃)₃Si}₂Te, and Methanol Taehong Gwon ¹ , Taeyong Eom ¹ , Sijung Yoo ¹ , Eui-sang Park ¹ , Sanggyun Kim ¹ , Chanyoung Yoo ¹ , Han-Koo Lee ² , Deok-Yong Cho ³ , Moo-sung Kim ⁴ , Iain Buchanan ⁵ , Manchao Xiao ⁵ , Sergei Ivanov ⁵ , and Cheol Seong Hwang ¹ <i>¹Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, National University, ²Pohang Accelerator Laboratory, ³IPIT & Department of Physics, Chonbuk National University, ⁴Versum Materials Korea, ⁵Versum Materials, Inc</i>
WA3-D-5 13:40-13:55	Involvement of an Intermediate Nonpolar Phase during Polarization Switching in the Hf_{0.4}Zr_{0.6}O₂ Thin Films Han Joon Kim, Min Hyuk Park, Young Hwan Lee, Yu Jin Kim, Taehwan Moon, Keum Do Kim, Seung Dam Hyun, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University</i>
WA3-D-6 13:55-14:10	Plasma Information Based Virtual Metrology (PI-VM) of Nitride Deposition in the Multi-Stack Plasma-Enhanced Chemical Vapor Deposition (PECVD) Hyun-Joon Roh ¹ , Seolhye Park ¹ , Yunchang Jang ¹ , Sangwon Ryu ¹ , Nam-Kyun Kim ¹ , Hyun-Chul Wang ² , Jaihyung Won ² , and Gon-Ho Kim ¹ <i>¹Department of Energy Systems Engineering, Seoul National University, ²Wonik IPS Ltd.</i>
WA3-D-7 14:10-14:25	The Growth Characteristics and Electrical Properties of Dy-Doped HfO₂ Thin Film by Atomic Layer Deposition Il-Kwon Oh and Hyungjun Kim <i>Electrical and Electronic Engineering, Yonsei University</i>